



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



企业QQ二维码

Features

- $BV_{CEO} > 50V$
- $I_C = 3A$ Continuous Collector Current
- $I_{CM} = 6A$ Peak Pulse Current
- $R_{CE(SAT)} = 75m\Omega$ for a Low Equivalent On-Resistance
- Low Saturation Voltage (200mV Max @ 1A)
- h_{FE} Characterized up to 6A

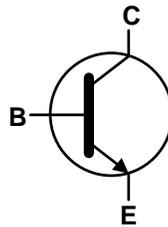
Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 Ⓜ3
- Weight: 0.015 grams (Approximate)

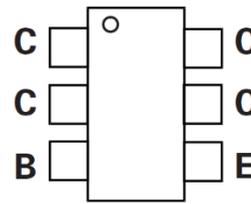
SOT26



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Base Voltage | V _{CBO} | 50 | V |
| Collector-Emitter Voltage | V _{CEO} | 50 | V |
| Emitter-Base Voltage | V _{EBO} | 5 | V |
| Base Current | I _B | 500 | mA |
| Continuous Collector Current | I _C | 3 | A |
| Peak Pulse Collector Current | I _{CM} | 6 | A |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

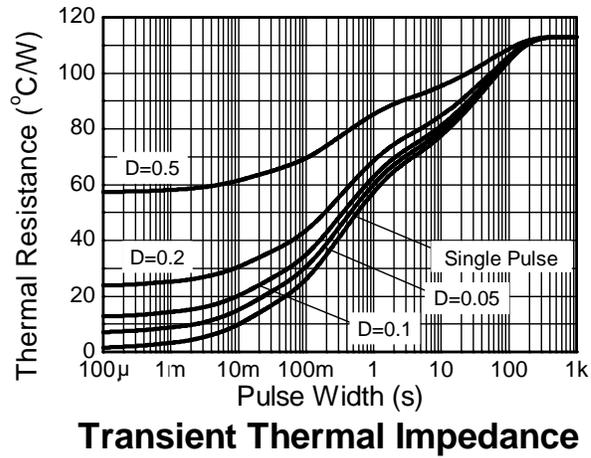
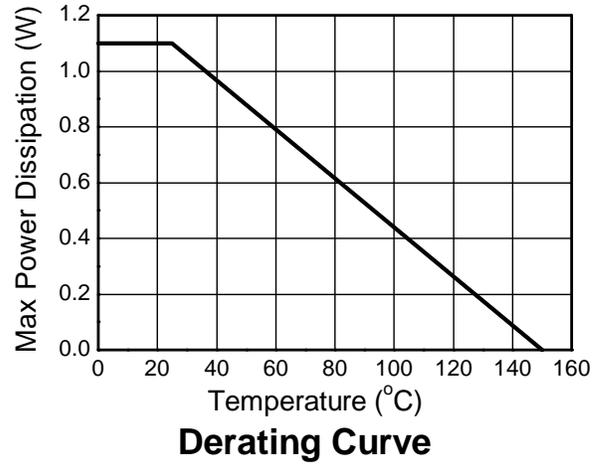
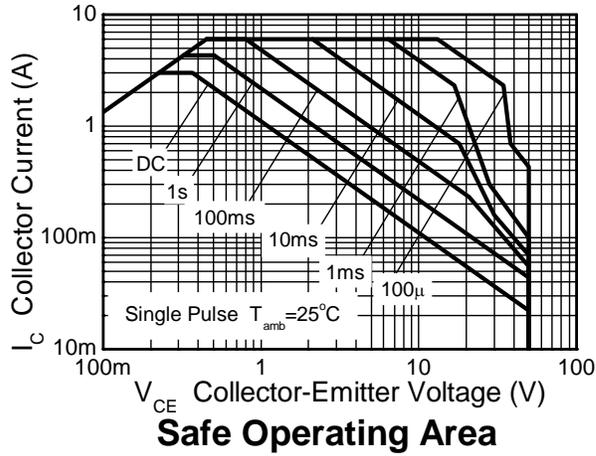
| Characteristic | Symbol | Value | Unit |
|---|-----------------------------------|-------------|-------|
| Power Dissipation | P _D | 1.1 | W |
| | | 8.8 | |
| Linear Derating Factor | | 1.7 | mW/°C |
| | | 13.6 | |
| Thermal Resistance, Junction to Ambient | R _{θJA} | 113 | °C/W |
| | | 73 | |
| Thermal Resistance, Junction to Lead | R _{θJL} | 18.6 | |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

ESD Ratings (Note 8)

| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V | 3A |
| Electrostatic Discharge - Machine Model | ESD MM | 400 | V | C |

- Notes:
- For a device mounted with the collector lead on 25mm x 25mm 1oz copper that is on single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 - Same as Note 5, except the device is measured at t ≤ 5 sec.
 - Thermal resistance from junction to solder-point (at the end of the collector lead).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

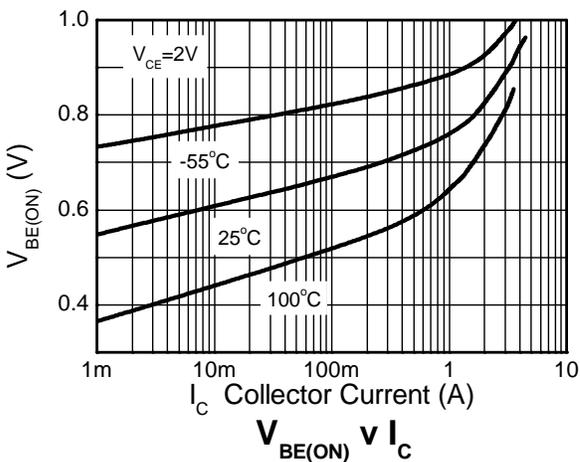
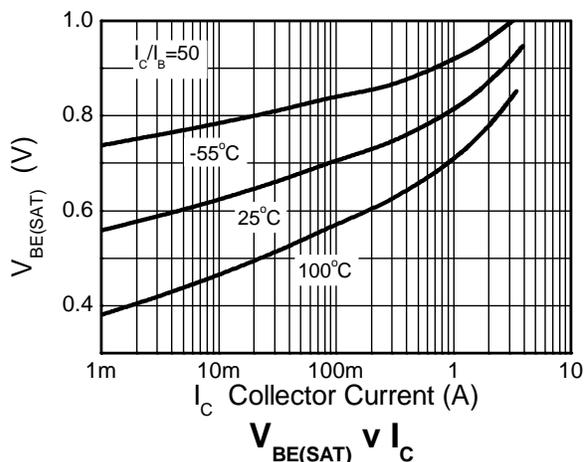
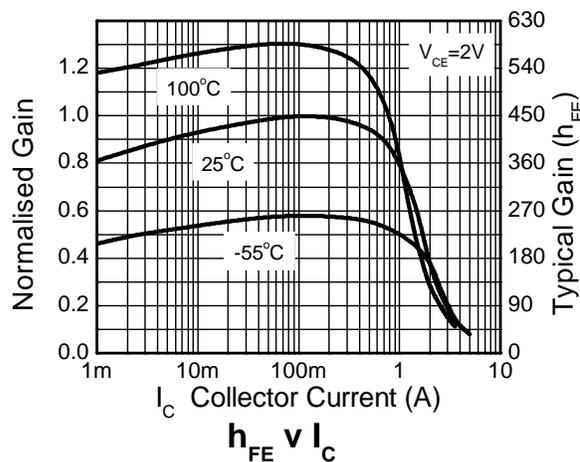
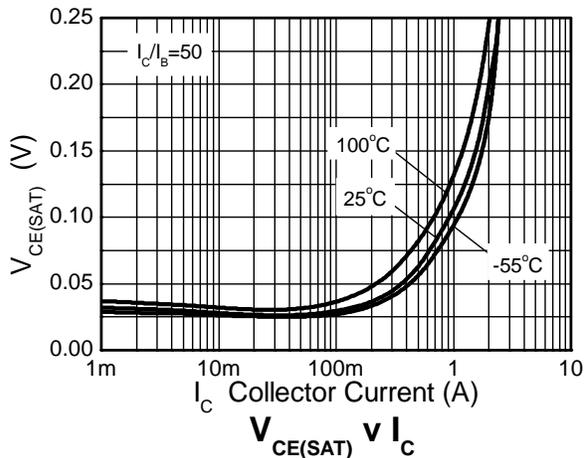
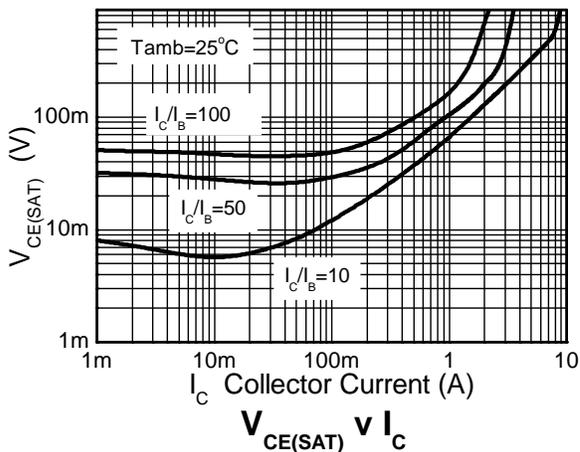


Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

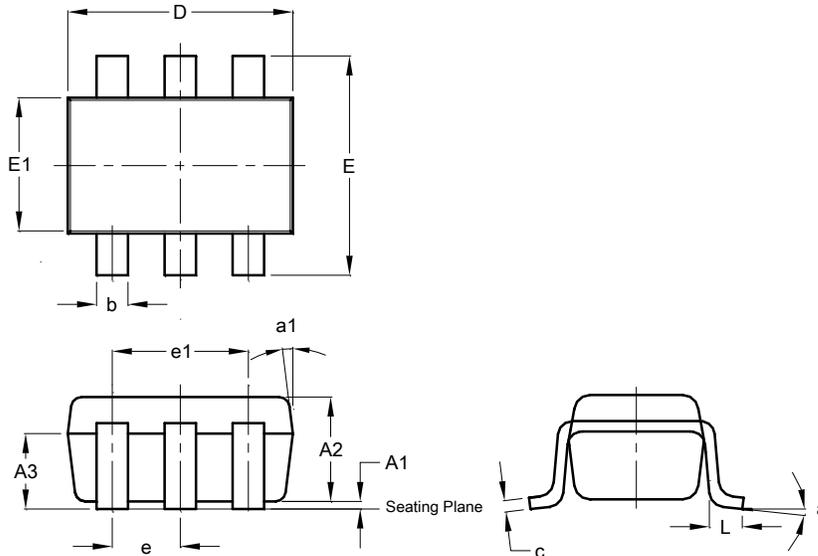
| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|--|---------------|-----|------|------|------|---|
| OFF CHARACTERISTICS | | | | | | |
| Collector-Base Breakdown Voltage | BV_{CBO} | 50 | 190 | — | V | $I_C = 100\mu\text{A}$ |
| Collector-Emitter Breakdown Voltage (Note 9) | BV_{CEO} | 50 | 65 | — | V | $I_C = 10\text{mA}$ |
| Emitter-Base Breakdown Voltage | BV_{EBO} | 5 | 8.3 | — | V | $I_E = 100\mu\text{A}$ |
| Collector-Base Cutoff Current | I_{CBO} | — | — | 100 | nA | $V_{CB} = 40\text{V}$ |
| Emitter Cutoff Current | I_{EBO} | — | — | 100 | nA | $V_{EB} = 4\text{V}$ |
| Collector-Emitter Cutoff Current | I_{CES} | — | — | 100 | nA | $V_{CES} = 40\text{V}$ |
| ON CHARACTERISTICS (Note 9) | | | | | | |
| DC Current Gain | h_{FE} | 200 | 400 | — | — | $I_C = 10\text{mA}, V_{CE} = 2\text{V}$ |
| | | 300 | 450 | — | | $I_C = 0.2\text{A}, V_{CE} = 2\text{V}$ |
| | | 200 | 400 | — | | $I_C = 1\text{A}, V_{CE} = 2\text{V}$ |
| | | 100 | 225 | — | | $I_C = 2\text{A}, V_{CE} = 2\text{V}$ |
| | | — | 40 | — | | $I_C = 6\text{A}, V_{CE} = 2\text{V}$ |
| Collector-Emitter Saturation Voltage | $V_{CE(SAT)}$ | — | 14 | 20 | mV | $I_C = 0.1\text{A}, I_B = 10\text{mA}$ |
| | | — | 145 | 200 | | $I_C = 1\text{A}, I_B = 10\text{mA}$ |
| | | — | 115 | 200 | | $I_C = 2\text{A}, I_B = 50\text{mA}$ |
| | | — | 225 | 300 | | $I_C = 3\text{A}, I_B = 100\text{mA}$ |
| Base-Emitter Saturation Voltage | $V_{BE(SAT)}$ | — | 0.93 | 1.0 | V | $I_C = 3\text{A}, I_B = 100\text{mA}$ |
| Base-Emitter Turn-On Voltage | $V_{BE(ON)}$ | — | 0.88 | 0.95 | V | $I_C = 3\text{A}, V_{CE} = 2\text{V}$ |
| SMALL SIGNAL CHARACTERISTICS | | | | | | |
| Current Gain-Bandwidth Product | f_T | 100 | 165 | — | MHz | $V_{CE} = 10\text{V}, I_C = 50\text{mA}, f = 100\text{MHz}$ |
| Output Capacitance | C_{obo} | — | 12 | 20 | pF | $V_{CB} = 10\text{V}, f = 1\text{MHz}$ |
| Turn-On Time | $t_{(on)}$ | — | 170 | — | ns | $V_{CC} = 10\text{V}, I_C = 1\text{A}$ |
| Turn-Off Time | $t_{(off)}$ | — | 750 | — | ns | $I_{B1} = I_{B2} = 10\text{mA}$ |

 Note: 9. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



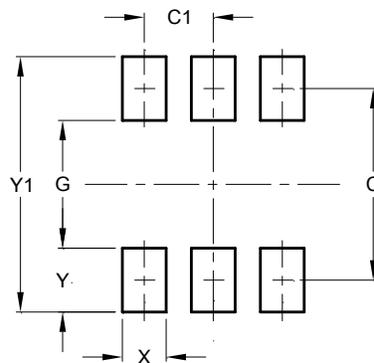
Package Outline Dimensions



| SOT26 | | | |
|-------|-------|------|------|
| Dim | Min | Max | Typ |
| A1 | 0.013 | 0.10 | 0.05 |
| A2 | 1.00 | 1.30 | 1.10 |
| A3 | 0.70 | 0.80 | 0.75 |
| b | 0.35 | 0.50 | 0.38 |
| c | 0.10 | 0.20 | 0.15 |
| D | 2.90 | 3.10 | 3.00 |
| e | - | - | 0.95 |
| e1 | - | - | 1.90 |
| E | 2.70 | 3.00 | 2.80 |
| E1 | 1.50 | 1.70 | 1.60 |
| L | 0.35 | 0.55 | 0.40 |
| a | - | - | 8° |
| a1 | - | - | 7° |

All Dimensions in mm

Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 2.40 |
| C1 | 0.95 |
| G | 1.60 |
| X | 0.55 |
| Y | 0.80 |
| Y1 | 3.20 |